

In the Abstract:

~~Method for fabricating a spacer structure~~

~~The invention relates to a~~ method for fabricating a spacer structure, ~~comprising the steps of~~includes: forming a gate insulation layer (2) having a gate deposition-inhibiting layer (2A), a gate layer (3) and a covering deposition-inhibiting layer (4) on a semiconductor substrate (1), and patterning the gate layer (3) and the covering deposition-inhibiting layer (4) in order to form gate stacks (G), ~~a~~. An insulation layer (6) ~~being~~is deposited selectively using the deposition-inhibiting layers, thereby (2A, 4) for the ~~purpose of~~permitting highly accurate formation of a the spacer structure.